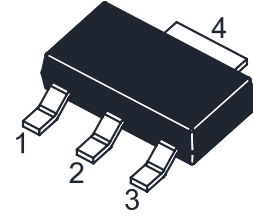
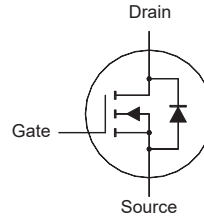


## N-Channel Enhancement Mode MOSFET

### Features

- AEC-Q101 Qualified
- Low threshold drive
- Halogen and Antimony Free(HAF),  
RoHS compliant



1.Gate 2.Drain 3.Source 4.Drain  
SOT-223 Plastic Package

### Applications

- Switching applications
- DC-DC converters for Telecom and Computer

### Key Parameters

Parameter	Value	Unit
$BV_{DSS}$	60	V
$R_{DS(ON)}$ Max	78 @ $V_{GS} = 10$ V	m $\Omega$
	100 @ $V_{GS} = 4.5$ V	
$V_{GS(th)}$ typ	1.7	V
$Q_g$ typ	4.3 @ $V_{GS} = 4.5$ V	nC

### Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_c = 25^\circ\text{C}$	4
		$T_c = 100^\circ\text{C}$	2.9
Peak Drain Current, Pulsed <sup>1)</sup>	$I_{DM}$	16	A
Single-Pulse Avalanche Current	$I_{AS}$	5.4	A
Single-Pulse Avalanche Energy <sup>2)</sup>	$E_{AS}$	1.5	mJ
Power Dissipation	$P_D$	1.25	W
Operating Junction and Storage Temperature Range	$T_j, T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance - Junction to Case	$R_{\theta JC}$	20	$^\circ\text{C/W}$
Thermal Resistance - Junction to Ambient <sup>3)</sup> Steady State	$R_{\theta JA}$	100	$^\circ\text{C/W}$

<sup>1)</sup> Pulse Test: Pulse Width  $\leq 100$   $\mu\text{s}$ , Duty Cycle  $\leq 2\%$ , Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)} = 150^\circ\text{C}$ .

<sup>2)</sup> Limited by  $T_{J(MAX)}$ , starting  $T_j = 25^\circ\text{C}$ ,  $L = 0.1$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 5.4$  A,  $V_{GS} = 10$  V.

<sup>3)</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at  $T_a = 25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>					
Drain-Source Breakdown Voltage at $I_D = 250 \mu\text{A}$	$BV_{DSS}$	60	-	-	V
Drain-Source Leakage Current at $V_{DS} = 48 \text{ V}$	$I_{DSS}$	-	-	1	$\mu\text{A}$
Gate Leakage Current at $V_{GS} = \pm 20 \text{ V}$	$I_{GSS}$	-	-	$\pm 100$	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	$V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance at $V_{GS} = 10 \text{ V}$ , $I_D = 2 \text{ A}$ at $V_{GS} = 4.5 \text{ V}$ , $I_D = 1.5 \text{ A}$	$R_{DS(on)}$	- -	68 -	78 100	$\text{m}\Omega$
<b>DYNAMIC PARAMETERS</b>					
Forward Transconductance at $V_{DS} = 5 \text{ V}$ , $I_D = 2 \text{ A}$	$g_{FS}$	-	3.9	-	S
Gate Resistance at $V_{DS} = 0 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	$R_g$	-	0.9	-	$\Omega$
Input Capacitance at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{iss}$	-	446.6	-	pF
Output Capacitance at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{oss}$	-	26	-	pF
Reverse Transfer Capacitance at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{rss}$	-	5	-	pF
Gate Charge Total at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$ at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 4.5 \text{ V}$ , $I_D = 3 \text{ A}$	$Q_g$	- -	8.1 4.3	- -	nC
Gate to Source Charge at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$	$Q_{gs}$	-	1.9	-	nC
Gate to Drain Charge at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$	$Q_{gd}$	-	1.9	-	nC
Turn-On Delay Time at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$ , $R_g = 4.7 \Omega$	$t_{d(on)}$	-	7	-	ns
Turn-On Rise Time at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$ , $R_g = 4.7 \Omega$	$t_r$	-	3	-	ns
Turn-Off Delay Time at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$ , $R_g = 4.7 \Omega$	$t_{d(off)}$	-	6	-	ns
Turn-Off Fall Time at $V_{DS} = 30 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$ , $R_g = 4.7 \Omega$	$t_f$	-	2	-	ns
<b>Body-Diode PARAMETERS</b>					
Drain-Source Diode Forward Voltage at $I_S = 4 \text{ A}$ , $V_{GS} = 0 \text{ V}$	$V_{SD}$	-	-	1.2	V
Body-Diode Continuous Current	$I_S$	-	-	4	A
Body-Diode Continuous Current, Pulsed	$I_{SM}$	-	-	16	A
Body Diode Reverse Recovery Time at $I_S = 4 \text{ A}$ , $di/dt = 100 \text{ A} / \mu\text{s}$	$t_{rr}$	-	8.4	-	ns
Body Diode Reverse Recovery Charge at $I_S = 4 \text{ A}$ , $di/dt = 100 \text{ A} / \mu\text{s}$	$Q_{rr}$	-	4.6	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

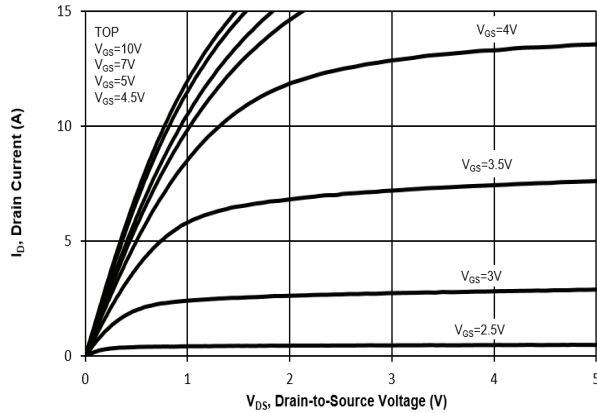


Fig. 2 Typical Transfer Characteristics

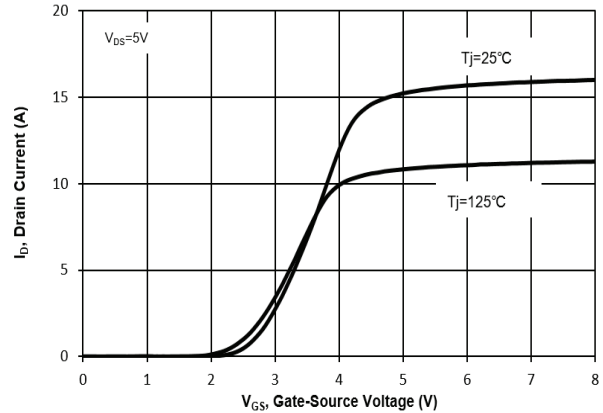


Fig. 3 On-Resistance vs. Drain Current

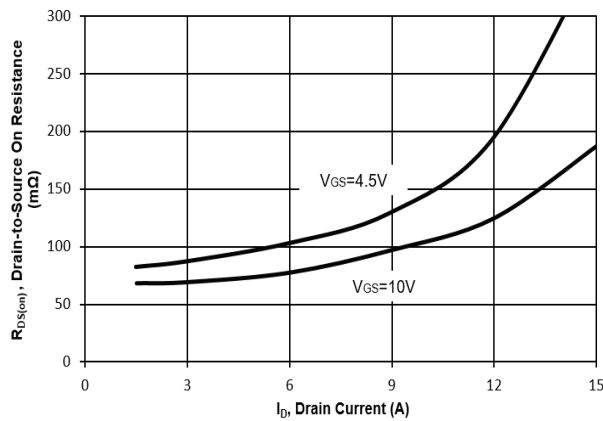


Fig. 4 On-Resistance vs. Gate to Source Voltage

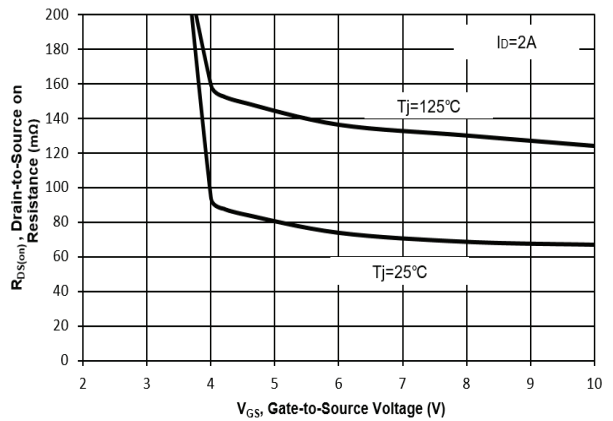


Fig. 5 On-Resistance vs.  $T_J$

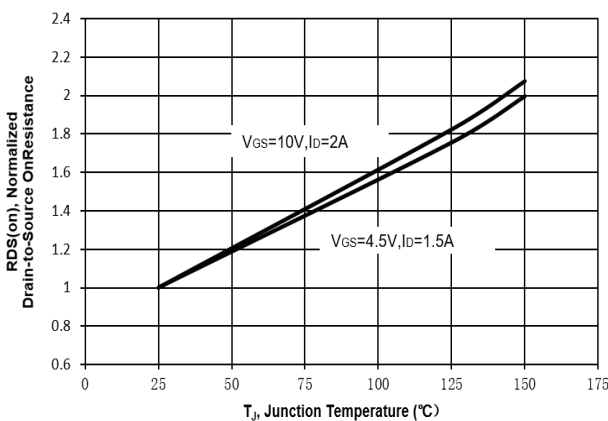
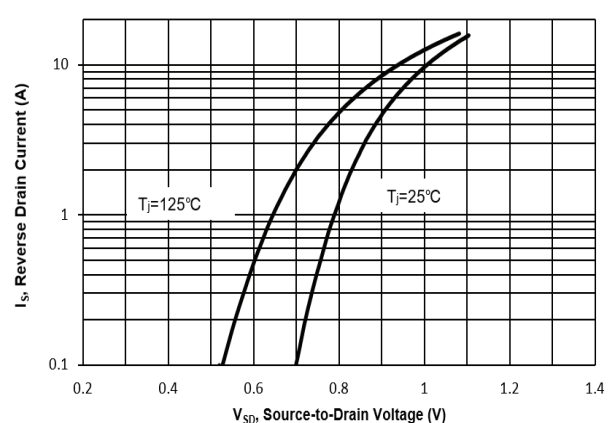


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

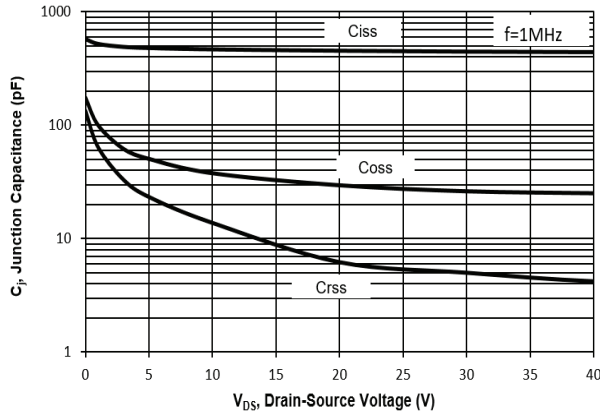


Fig. 8 Drain-Source Leakage Current vs. T<sub>J</sub>

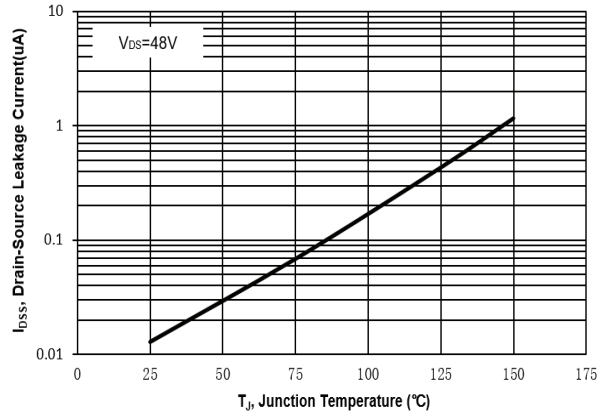


Fig. 9 V<sub>(BR)DSS</sub> vs. Junction Temperature

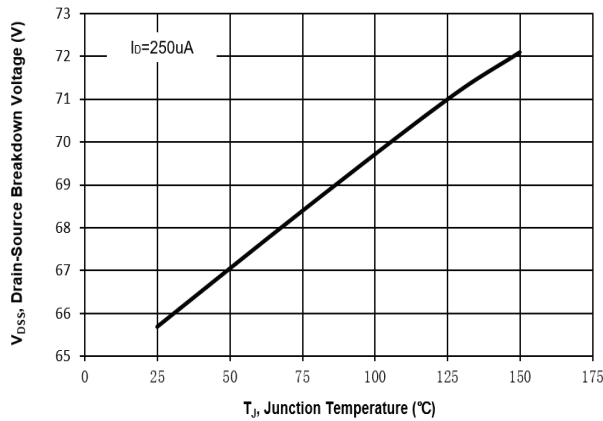


Fig. 10 Gate Threshold Variation vs. T<sub>J</sub>

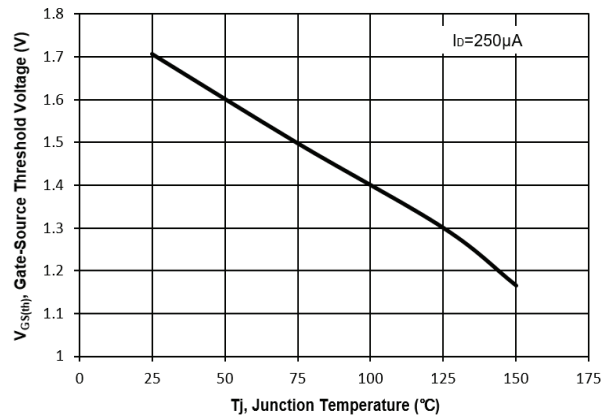


Fig. 11 Gate Charge

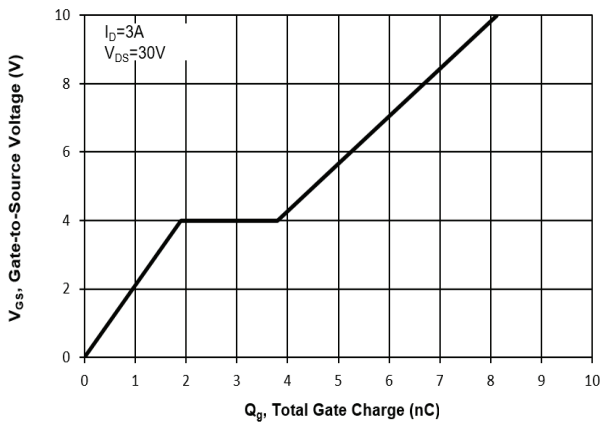
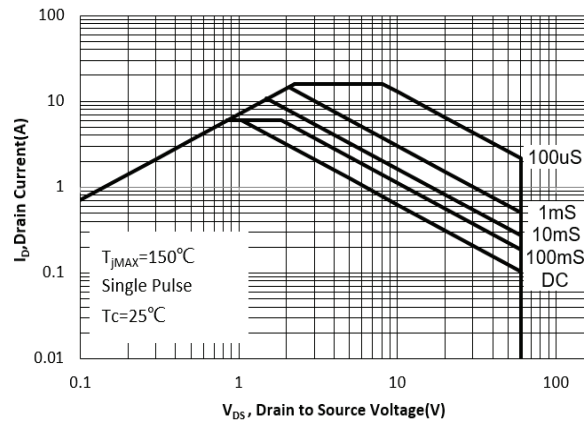
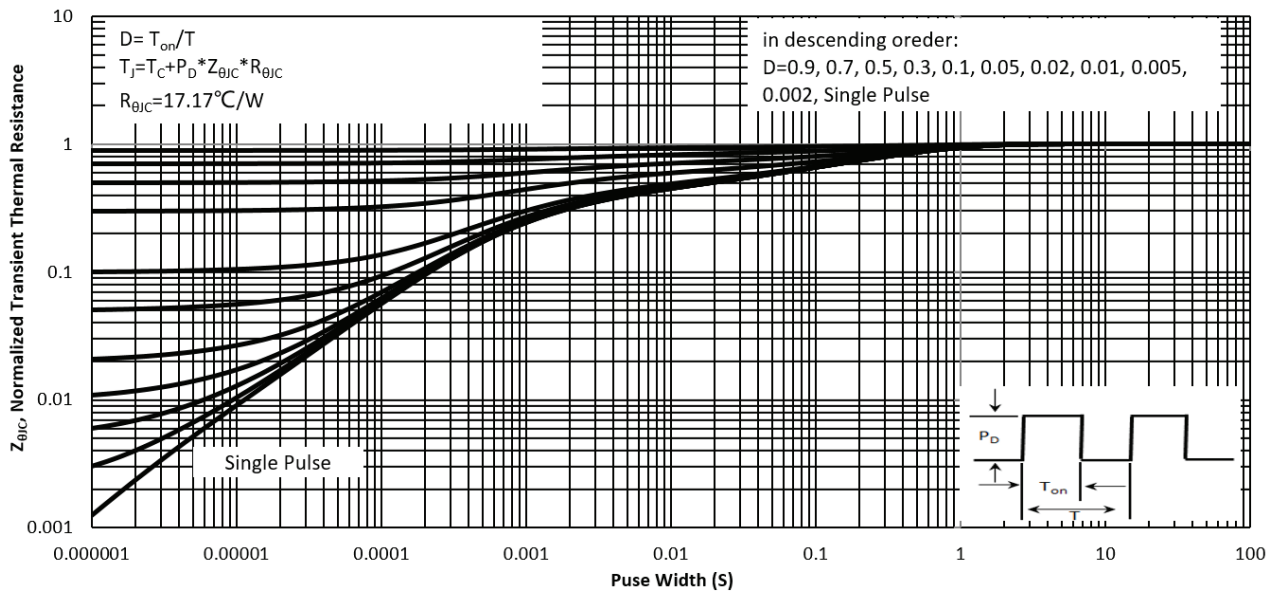


Fig. 12 Safe Operation Area

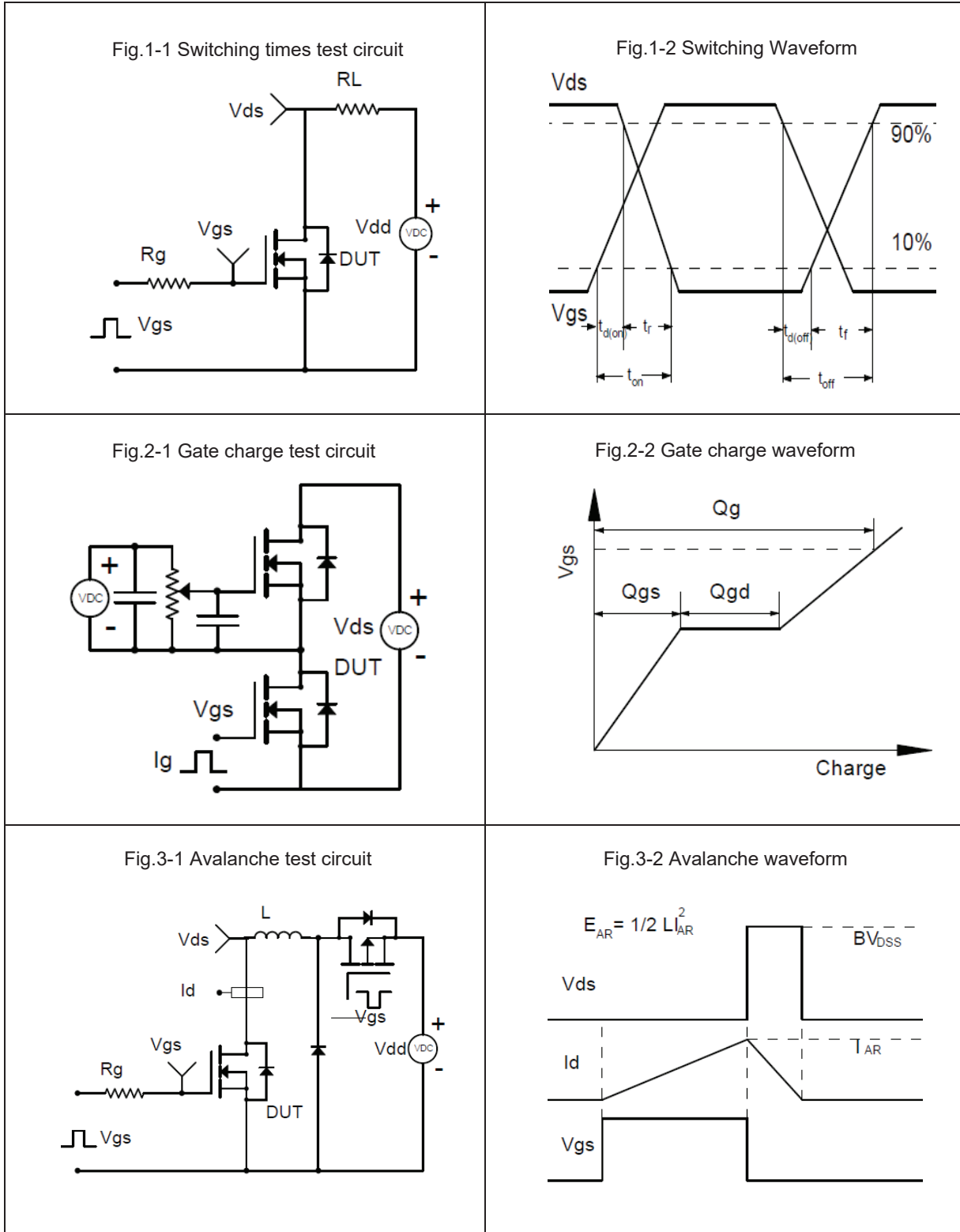


Electrical Characteristics Curves

Fig.13 Normalized Maximum Transient Thermal Impedance( $z_{\theta JC}$ )

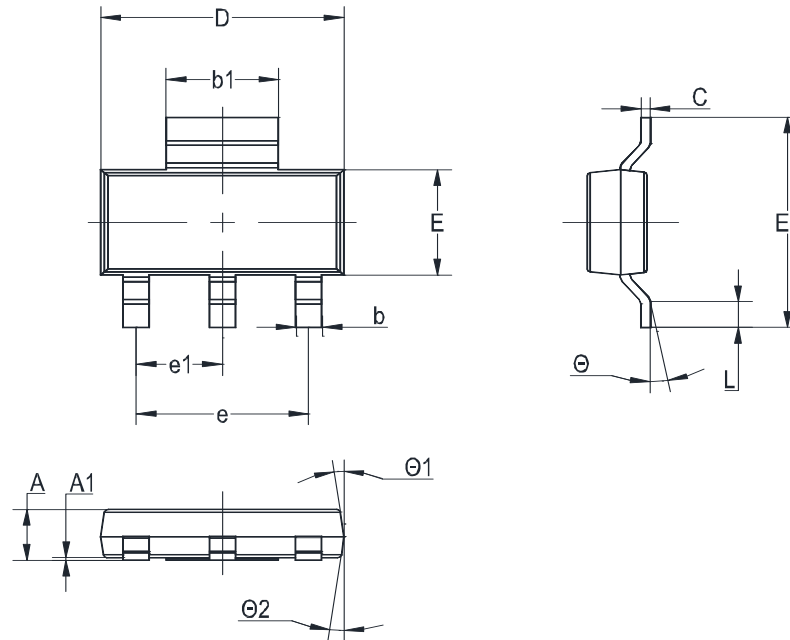


Test Circuits



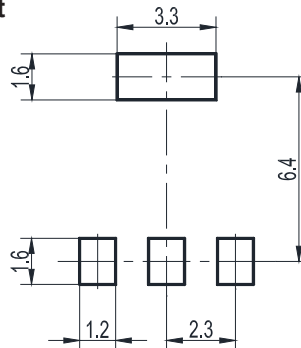
Package Outline (Dimensions in mm)

SOT-223



Unit	A	A1	b	b1	C	D	E	E1	e	e1	L	Θ	Θ1	Θ2
mm	1.8	0.1	0.8	3.1	0.32	6.7	3.7	7.3	4.6	2.3	1.1	10°	7°	7°
	1.5	MAX	0.6	2.9	0.22	6.3	3.3	6.7	TYP	TYP	0.7	0°	0°	0°

Recommended Soldering Footprint



Packing information

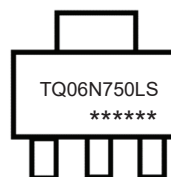
Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

Marking information

" TQ06N750LS " = Part No.

" \*\*\*\*\* " = Date Code Marking

Font type: Arial



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